

## IN THE CLAIMS

1 (Previously Presented). A reflector comprising:  
a reflective layer; and  
an absorbing layer to selectively absorb blue light, said absorbing layer being located over said reflective layer, said absorbing layer including about 700 to about 750 Angstroms of silicon dioxide and about 700 to about 750 Angstroms of silicon nitride.

2 (Original). The reflector of claim 1 wherein said reflector is a micromirror.

3 (Original). The reflector of claim 1 wherein said reflective layer is formed of silver, said silver being formed over a polished semiconductor material.

Claims 4-7 (Canceled).

8 (Currently Amended). A method comprising:  
forming a reflective layer; and  
forming an absorbing layer, including an oxide layer and ~~an~~ a nitride layer, each of a thickness of about 700 Angstroms to about 750 Angstroms, over said reflective layer at a temperature of less than 250°C so that said layers selectively absorb blue light.

9 (Previously Presented). The method of claim 8 including forming the reflective layer by depositing silver directly on a semiconductor layer.

10 (Original). The method of claim 8 including forming an absorbing layer including a layer of two different insulator materials.

11 (Original). The method of claim 9 including forming said silver layer at a temperature of 50°C or less.

Claim 12 (Canceled).

13 (Previously Presented). The method of claim 8 including forming said absorbing layer using chemical vapor deposition.

Claims 14-15 (Canceled).

16 (Previously Presented). A reflector comprising:  
a silicon substrate;  
a silver layer formed directly on said silicon substrate; and  
an absorbing layer over said silver layer, said absorbing layer including about 700 to 750 Angstroms of silicon dioxide and from 700 to about 750 Angstroms of silicon nitride, said absorbing layer selectively absorbing blue light.

17 (Original). The reflector of claim 16 wherein said reflector is a micromirror.

Claims 18-22 (Canceled).

23 (Original). The reflector of claim 16 wherein said silver layer is formed at a temperature below 50°C.

24 (Previously Presented). The reflector of claim 16 wherein said absorbing layer is formed at a temperature below 250°C.

Claims 25-30 (Canceled).